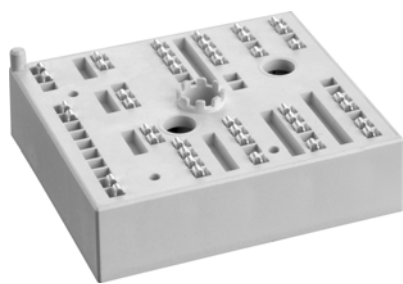


# SKiiP 24AC12T7V1



MiniSKiiP® 2

## Sixpack

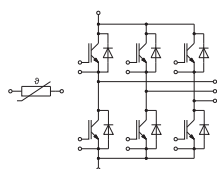
### SKiiP 24AC12T7V1

#### Features\*

- 1200V Generation 7 IGBTs (T7)
- Robust and soft switching freewheeling diodes in CAL technology
- Highly reliable spring contacts for electrical connections
- UL recognized: File no. E63532

#### Remarks

- Max. case temperature limited to  $T_C = T_S = 125^\circ\text{C}$
- Product reliability results valid for  $T_j \leq 150^\circ\text{C}$ ;  $T_{j,op} > 150^\circ\text{C}$  during overload (Details see AN19-002)
- MiniSKiiP "Technical Explanations" and "Mounting Instructions" are part of the data sheet. Please refer to both documents for further information.
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AC

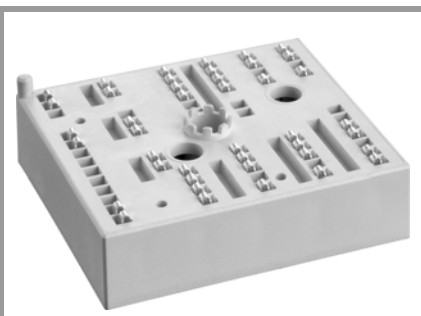
#### Absolute Maximum Ratings

| Symbol                 | Conditions                                                                           | Values                    | Unit             |
|------------------------|--------------------------------------------------------------------------------------|---------------------------|------------------|
| <b>Inverter - IGBT</b> |                                                                                      |                           |                  |
| $V_{CES}$              | $T_j = 25^\circ\text{C}$                                                             | 1200                      | V                |
| $I_C$                  | $\lambda_{paste}=0.8\text{ W/(mK)}$                                                  | $T_s = 70^\circ\text{C}$  | A                |
|                        | $T_j = 175^\circ\text{C}$                                                            | $T_s = 100^\circ\text{C}$ | A                |
| $I_C$                  | $\lambda_{paste}=2.5\text{ W/(mK)}$                                                  | $T_s = 70^\circ\text{C}$  | A                |
|                        | $T_j = 175^\circ\text{C}$                                                            | $T_s = 100^\circ\text{C}$ | A                |
| $I_{Cnom}$             |                                                                                      | 35                        | A                |
| $I_{CRM}$              |                                                                                      | 70                        | A                |
| $V_{GES}$              |                                                                                      | -20 ... 20                | V                |
| $t_{psc}$              | $V_{CC} = 800\text{ V}$<br>$V_{GE} \leq 15\text{ V}$<br>$V_{CES} \leq 1200\text{ V}$ | $T_j = 175^\circ\text{C}$ | $\mu\text{s}$    |
| $T_j$                  |                                                                                      | -40 ... 175               | $^\circ\text{C}$ |
| <b>Inverse - Diode</b> |                                                                                      |                           |                  |
| $V_{RRM}$              | $T_j = 25^\circ\text{C}$                                                             | 1200                      | V                |
| $I_F$                  | $\lambda_{paste}=0.8\text{ W/(mK)}$                                                  | $T_s = 70^\circ\text{C}$  | A                |
|                        | $T_j = 175^\circ\text{C}$                                                            | $T_s = 100^\circ\text{C}$ | A                |
| $I_F$                  | $\lambda_{paste}=2.5\text{ W/(mK)}$                                                  | $T_s = 70^\circ\text{C}$  | A                |
|                        | $T_j = 175^\circ\text{C}$                                                            | $T_s = 100^\circ\text{C}$ | A                |
| $I_{FRM}$              |                                                                                      | 70                        | A                |
| $I_{FSM}$              | $t_p = 10\text{ ms, sin } 180^\circ, T_j = 150^\circ\text{C}$                        | 170                       | A                |
| $T_j$                  |                                                                                      | -40 ... 175               | $^\circ\text{C}$ |
| <b>Module</b>          |                                                                                      |                           |                  |
| $I_{t(RMS)}$           | $T_{terminal} = 80^\circ\text{C}, 20\text{ A per spring}$                            | 100                       | A                |
| $T_{stg}$              | module without TIM                                                                   | -40 ... 125               | $^\circ\text{C}$ |
| $V_{isol}$             | AC sinus 50 Hz, $t = 1\text{ min}$                                                   | 2500                      | V                |

#### Characteristics

| Symbol                 | Conditions                                                            | min.                      | typ. | max. | Unit             |
|------------------------|-----------------------------------------------------------------------|---------------------------|------|------|------------------|
| <b>Inverter - IGBT</b> |                                                                       |                           |      |      |                  |
| $V_{CE(sat)}$          | $I_C = 35\text{ A}$                                                   | $T_j = 25^\circ\text{C}$  | 1.60 | 1.75 | V                |
|                        | $V_{GE} = 15\text{ V}$                                                | $T_j = 150^\circ\text{C}$ | 1.78 | 1.93 | V                |
|                        | chiplevel                                                             | $T_j = 175^\circ\text{C}$ | 1.82 | 1.97 | V                |
| $V_{CE0}$              |                                                                       | $T_j = 25^\circ\text{C}$  | 1.00 | 1.05 | V                |
|                        | chiplevel                                                             | $T_j = 150^\circ\text{C}$ | 0.80 | 0.85 | V                |
|                        |                                                                       | $T_j = 175^\circ\text{C}$ | 0.75 | 0.80 | V                |
| $r_{CE}$               | $V_{GE} = 15\text{ V}$                                                | $T_j = 25^\circ\text{C}$  | 17   | 20   | $\text{m}\Omega$ |
|                        | chiplevel                                                             | $T_j = 150^\circ\text{C}$ | 28   | 31   | $\text{m}\Omega$ |
|                        |                                                                       | $T_j = 175^\circ\text{C}$ | 31   | 33   | $\text{m}\Omega$ |
| $V_{GE(th)}$           | $V_{GE} = V_{CE}, I_C = 0.75\text{ mA}$                               | 5.15                      | 5.8  | 6.45 | V                |
| $I_{CES}$              | $V_{GE} = 0\text{ V}, V_{CE} = 1200\text{ V}, T_j = 25^\circ\text{C}$ |                           |      | 1    | mA               |
| $C_{ies}$              | $V_{CE} = 25\text{ V}$                                                | $f = 1\text{ MHz}$        | 6.60 |      | nF               |
| $C_{oes}$              | $V_{GE} = 0\text{ V}$                                                 | $f = 1\text{ MHz}$        | 0.09 |      | nF               |
| $C_{res}$              |                                                                       | $f = 1\text{ MHz}$        | 0.02 |      | nF               |
| $Q_G$                  | $V_{GE} = -8\text{ V} \dots +15\text{ V}$                             |                           | 490  |      | nC               |
| $R_{Gint}$             | $T_j = 25^\circ\text{C}$                                              |                           | 0    |      | $\Omega$         |

# SKiiP 24AC12T7V1



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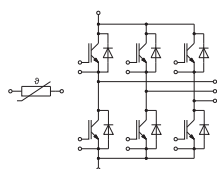
### SKiiP 24AC12T7V1

#### Features\*

- 1200V Generation 7 IGBTs (T7)
- Robust and soft switching freewheeling diodes in CAL technology
- Highly reliable spring contacts for electrical connections
- UL recognized: File no. E63532

#### Remarks

- Max. case temperature limited to  $T_C = T_S = 125^\circ\text{C}$
- Product reliability results valid for  $T_J \leq 150^\circ\text{C}$ ;  $T_{J,op} > 150^\circ\text{C}$  during overload (Details see AN19-002)
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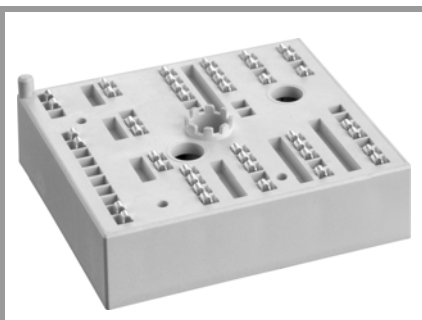


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| Characteristics        |                                                                                                                                                             |                           |      |      |           |
|------------------------|-------------------------------------------------------------------------------------------------------------------------------------------------------------|---------------------------|------|------|-----------|
| Symbol                 | Conditions                                                                                                                                                  |                           | min. | typ. | max. Unit |
| <b>Inverter - IGBT</b> |                                                                                                                                                             |                           |      |      |           |
| $t_{d(on)}$            | $V_{CC} = 600\text{ V}$<br>$I_C = 35\text{ A}$<br>$R_{G\ on} = 9.1\ \Omega$<br>$R_{G\ off} = 9.1\ \Omega$<br>$V_{GE} = +15/-15\text{ V}$                    | $T_J = 25^\circ\text{C}$  |      | 37   | ns        |
|                        |                                                                                                                                                             | $T_J = 150^\circ\text{C}$ |      | 39   | ns        |
|                        |                                                                                                                                                             | $T_J = 175^\circ\text{C}$ |      | 40   | ns        |
| $t_r$                  |                                                                                                                                                             | $T_J = 25^\circ\text{C}$  |      | 37   | ns        |
|                        |                                                                                                                                                             | $T_J = 150^\circ\text{C}$ |      | 43   | ns        |
|                        |                                                                                                                                                             | $T_J = 175^\circ\text{C}$ |      | 46   | ns        |
| $E_{on}$               | $R_{G\ on} = 9.1\ \Omega$<br>$R_{G\ off} = 9.1\ \Omega$<br>$V_{GE} = +15/-15\text{ V}$                                                                      | $T_J = 25^\circ\text{C}$  |      | 3.1  | mJ        |
|                        |                                                                                                                                                             | $T_J = 150^\circ\text{C}$ |      | 4.4  | mJ        |
|                        |                                                                                                                                                             | $T_J = 175^\circ\text{C}$ |      | 4.6  | mJ        |
| $t_{d(off)}$           |                                                                                                                                                             | $T_J = 25^\circ\text{C}$  |      | 231  | ns        |
|                        |                                                                                                                                                             | $T_J = 150^\circ\text{C}$ |      | 321  | ns        |
|                        |                                                                                                                                                             | $T_J = 175^\circ\text{C}$ |      | 346  | ns        |
| $t_f$                  | @ $T_J = 150^\circ\text{C}$ :<br>$di/dt_{on} = 860\text{ A}/\mu\text{s}$<br>$di/dt_{off} = 380\text{ A}/\mu\text{s}$<br>$dv/dt = 3610\text{ V}/\mu\text{s}$ | $T_J = 25^\circ\text{C}$  |      | 48   | ns        |
|                        |                                                                                                                                                             | $T_J = 150^\circ\text{C}$ |      | 74   | ns        |
|                        |                                                                                                                                                             | $T_J = 175^\circ\text{C}$ |      | 90   | ns        |
| $E_{off}$              |                                                                                                                                                             | $T_J = 25^\circ\text{C}$  |      | 2.3  | mJ        |
|                        |                                                                                                                                                             | $T_J = 150^\circ\text{C}$ |      | 3.9  | mJ        |
|                        |                                                                                                                                                             | $T_J = 175^\circ\text{C}$ |      | 4.2  | mJ        |
| $R_{th(j-s)}$          | per IGBT, $\lambda_{paste} = 0.8\text{ W}/(\text{mK})$                                                                                                      |                           |      | 1.12 | K/W       |
| $R_{th(j-s)}$          | per IGBT, $\lambda_{paste} = 2.5\text{ W}/(\text{mK})$                                                                                                      |                           |      | 0.93 | K/W       |

| Characteristics        |                                                                               |                           |      |      |           |
|------------------------|-------------------------------------------------------------------------------|---------------------------|------|------|-----------|
| Symbol                 | Conditions                                                                    |                           | min. | typ. | max. Unit |
| <b>Inverse - Diode</b> |                                                                               |                           |      |      |           |
| $V_F = V_{EC}$         | $I_F = 35\text{ A}$<br>$V_{GE} = 0\text{ V}$<br>chipelevel                    | $T_J = 25^\circ\text{C}$  |      | 2.30 | 2.62 V    |
|                        |                                                                               | $T_J = 150^\circ\text{C}$ |      | 2.29 | 2.62 V    |
|                        |                                                                               | $T_J = 175^\circ\text{C}$ |      | 2.14 | 2.46 V    |
| $V_{F0}$               | chipelevel                                                                    | $T_J = 25^\circ\text{C}$  |      | 1.30 | 1.50 V    |
|                        |                                                                               | $T_J = 150^\circ\text{C}$ |      | 0.90 | 1.10 V    |
|                        |                                                                               | $T_J = 175^\circ\text{C}$ |      | 0.82 | 0.98 V    |
| $r_F$                  | chipelevel                                                                    | $T_J = 25^\circ\text{C}$  |      | 29   | 32 mΩ     |
|                        |                                                                               | $T_J = 150^\circ\text{C}$ |      | 40   | 43 mΩ     |
|                        |                                                                               | $T_J = 175^\circ\text{C}$ |      | 38   | 42 mΩ     |
| $I_{RRM}$              | $I_F = 35\text{ A}$<br>$V_{GE} = +15/-15\text{ V}$<br>$V_{CC} = 600\text{ V}$ | $T_J = 25^\circ\text{C}$  |      | 22   | A         |
|                        |                                                                               | $T_J = 150^\circ\text{C}$ |      | 28   | A         |
|                        |                                                                               | $T_J = 175^\circ\text{C}$ |      | 33   | A         |
| $Q_{rr}$               |                                                                               | $T_J = 25^\circ\text{C}$  |      | 2    | μC        |
|                        |                                                                               | $T_J = 150^\circ\text{C}$ |      | 5.2  | μC        |
|                        |                                                                               | $T_J = 175^\circ\text{C}$ |      | 5.7  | μC        |
| $E_{rr}$               | @ $T_J = 150^\circ\text{C}$ :<br>$di/dt_{off} = 870\text{ A}/\mu\text{s}$     | $T_J = 25^\circ\text{C}$  |      | 0.61 | mJ        |
|                        |                                                                               | $T_J = 150^\circ\text{C}$ |      | 2    | mJ        |
|                        |                                                                               | $T_J = 175^\circ\text{C}$ |      | 2.6  | mJ        |
| $R_{th(j-s)}$          | per Diode, $\lambda_{paste} = 0.8\text{ W}/(\text{mK})$                       |                           |      | 1.34 | K/W       |
| $R_{th(j-s)}$          | per Diode, $\lambda_{paste} = 2.5\text{ W}/(\text{mK})$                       |                           |      | 1.13 | K/W       |
| <b>Module</b>          |                                                                               |                           |      |      |           |
| $L_{CE}$               |                                                                               |                           |      | -    | nH        |
| $M_s$                  | to heat sink                                                                  |                           | 2    | 2.5  | Nm        |
| $w$                    |                                                                               |                           |      | 55   | g         |

# SKiiP 24AC12T7V1



MiniSKiiP® 2

| Characteristics    |                                                                                                                                                                                                   |      |                |      |          |
|--------------------|---------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------|------|----------------|------|----------|
| Symbol             | Conditions                                                                                                                                                                                        | min. | typ.           | max. | Unit     |
| Temperature Sensor |                                                                                                                                                                                                   |      |                |      |          |
| $R_{100}$          | $T_r=100^{\circ}\text{C}$ ( $R_{25}=1000\Omega$ )                                                                                                                                                 |      | $1670 \pm 3\%$ |      | $\Omega$ |
| $R_{(T)}$          | $R_{(T)}=1000\Omega[1+A(T-25^{\circ}\text{C})+B(T-25^{\circ}\text{C})^2]$<br>$A = 7.635 \cdot 10^{-3} \text{ }^{\circ}\text{C}^{-1}$ ,<br>$B = 1.731 \cdot 10^{-5} \text{ }^{\circ}\text{C}^{-2}$ |      |                |      |          |

## Sixpack

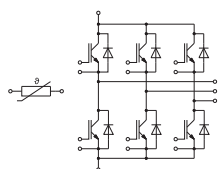
### SKiiP 24AC12T7V1

#### Features\*

- 1200V Generation 7 IGBTs (T7)
- Robust and soft switching freewheeling diodes in CAL technology
- Highly reliable spring contacts for electrical connections
- UL recognized: File no. E63532

#### Remarks

- Max. case temperature limited to  $T_C=T_S=125^{\circ}\text{C}$
- Product reliability results valid for  $T_j \leq 150^{\circ}\text{C}$ ;  $T_{j,op} > 150^{\circ}\text{C}$  during overload (Details see AN19-002)
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AC

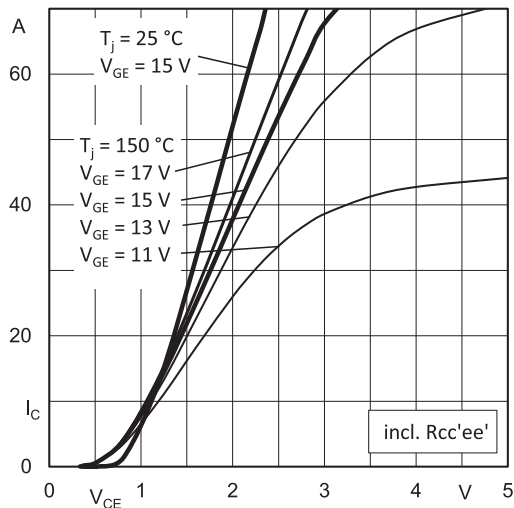


Fig. 1: Typ. output characteristic

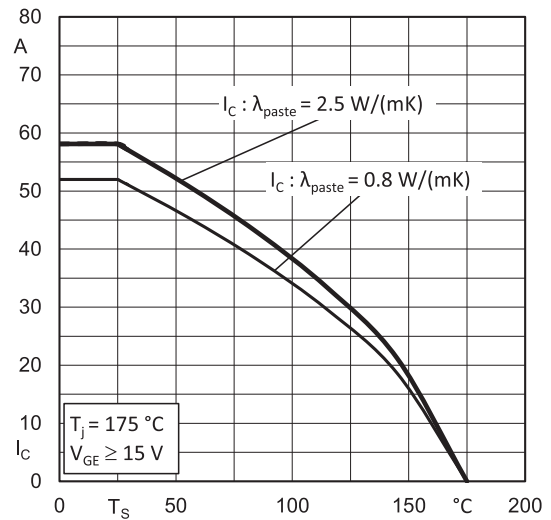


Fig. 2: Rated current vs. temperature  $I_C = f(T_S)$

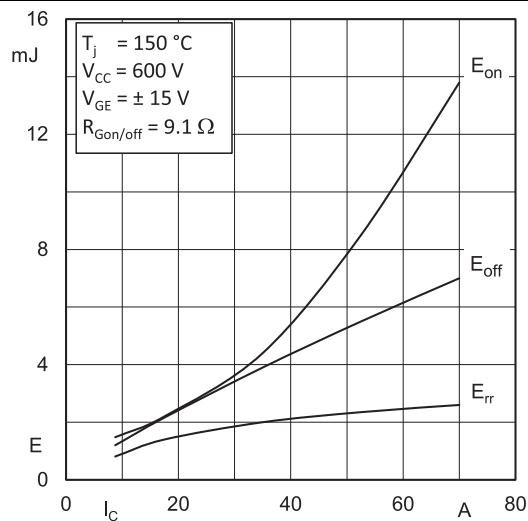


Fig. 3: Typ. turn-on /-off energy =  $f(I_C)$

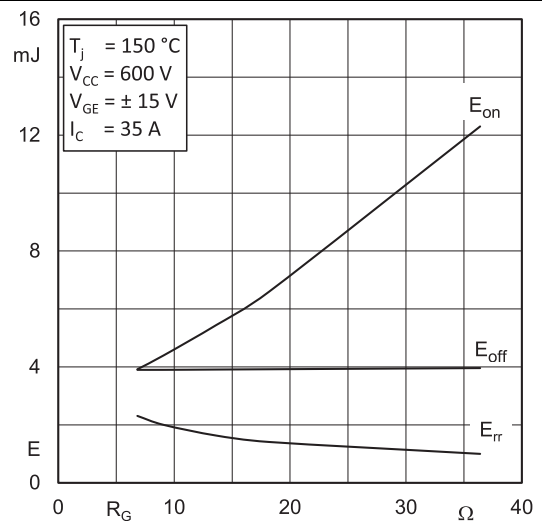


Fig. 4: Typ. turn-on /-off energy =  $f(R_G)$

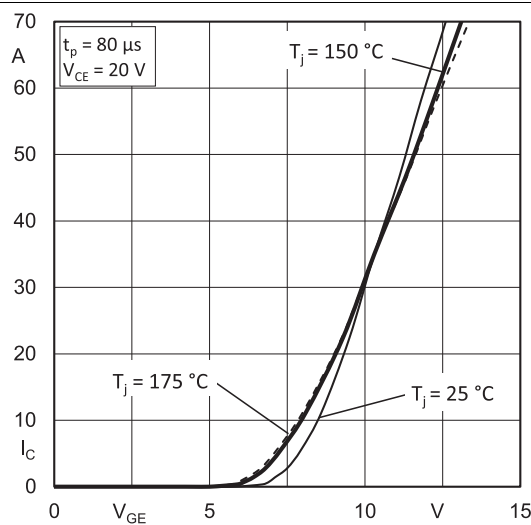


Fig. 5: Typ. transfer characteristic

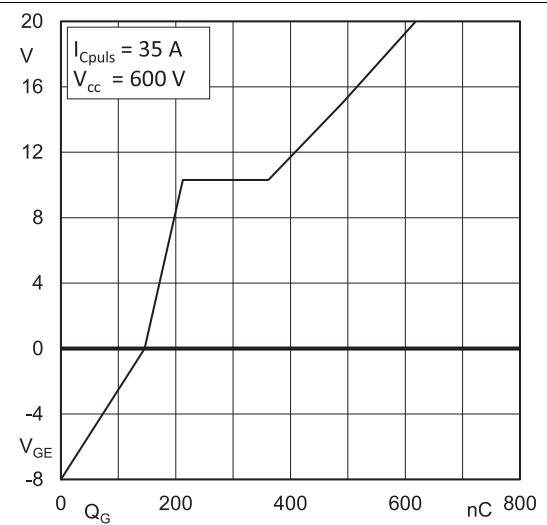


Fig. 6: Typ. gate charge characteristic

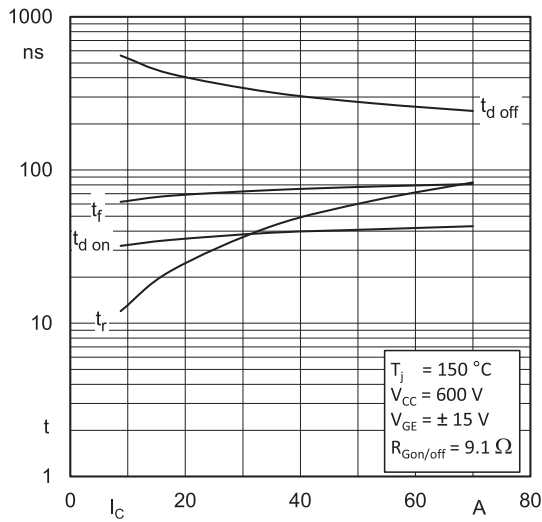


Fig. 7: Typ. switching times vs.  $I_C$

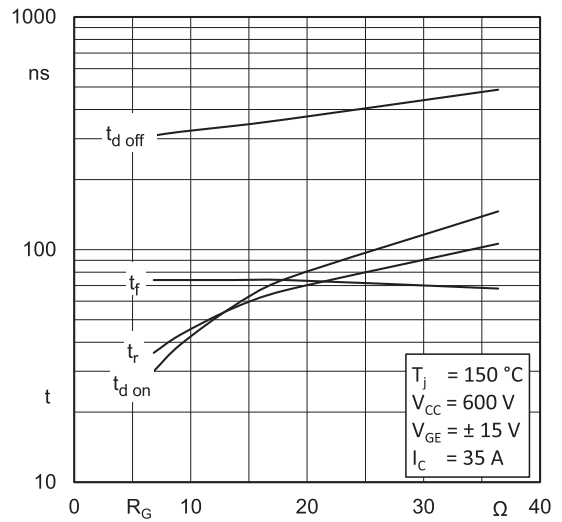


Fig. 8: Typ. switching times vs. gate resistor  $R_G$

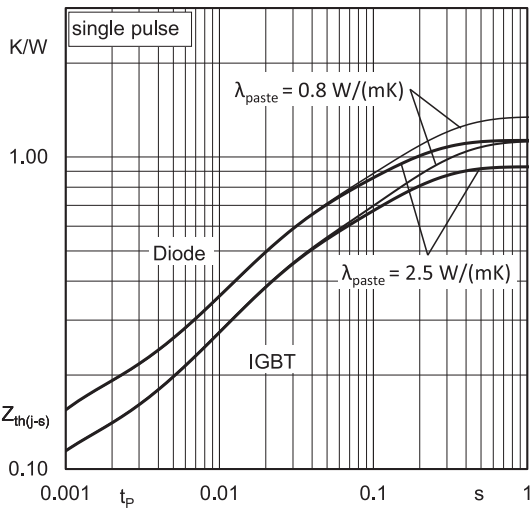


Fig. 9: Typ. transient thermal impedance

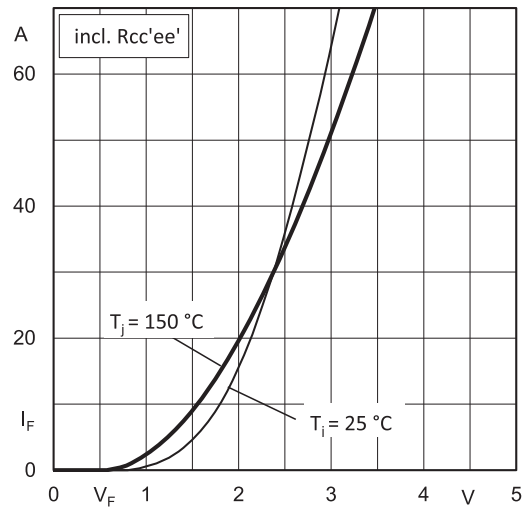


Fig. 10: Typ. CAL diode forward characteristic

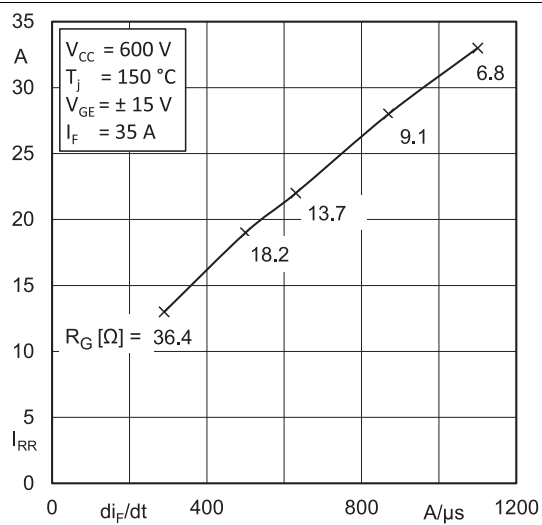


Fig. 11: Typ. CAL diode peak reverse recovery current

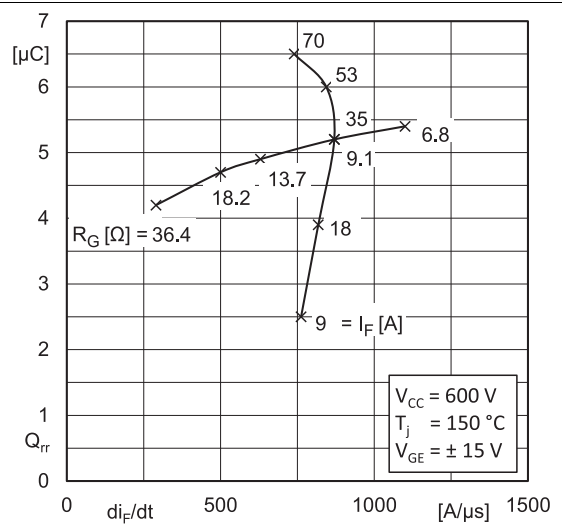
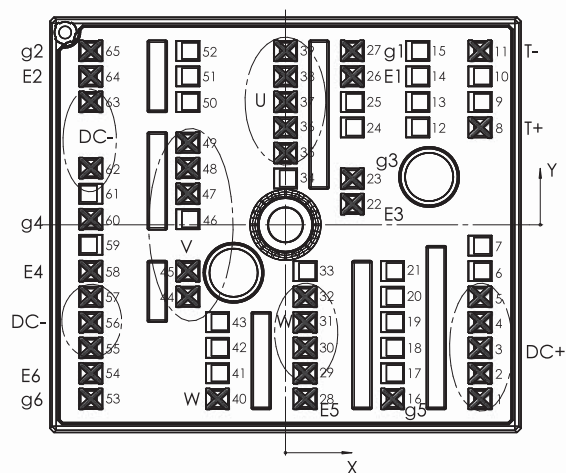


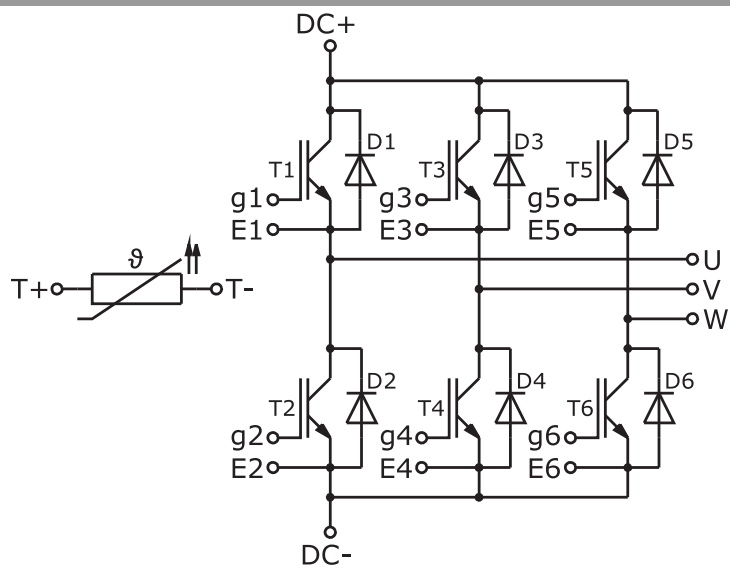
Fig. 12: Typ. CAL diode recovery charge

| Pin out |       |       |          |     |        |       |          |     |        |       |          |
|---------|-------|-------|----------|-----|--------|-------|----------|-----|--------|-------|----------|
| Pin     | X     | Y     | Function | Pin | X      | Y     | Function | Pin | X      | Y     | Function |
| 1       | 24,38 | -21,8 | DC+      | 23  | 8,38   | 5,8   | g3       | 45  | -12,23 | -5,8  | V        |
| 2       | 24,38 | -18,6 | DC+      | 24  |        |       |          | 46  |        |       |          |
| 3       | 24,38 | -15,4 | DC+      | 25  |        |       |          | 47  | -12,23 | 3,9   | V        |
| 4       | 24,38 | -12,2 | DC+      | 26  | 8,38   | 18,6  | E1       | 48  | -12,23 | 7,1   | V        |
| 5       | 24,38 | -9    | DC+      | 27  | 8,38   | 21,8  | g1       | 49  | -12,23 | 10,3  | V        |
| 6       |       |       |          | 28  | 2,46   | -21,8 | E5       | 50  |        |       |          |
| 7       |       |       |          | 29  | 2,46   | -18,6 | W        | 51  |        |       |          |
| 8       | 24,38 | 12,2  | T+       | 30  | 2,46   | -15,4 | W        | 52  |        |       |          |
| 9       |       |       |          | 31  | 2,46   | -12,2 | W        | 53  | -24,38 | -21,8 | g6       |
| 10      |       |       |          | 32  | 2,46   | -9    | W        | 54  | -24,38 | -18,6 | E6       |
| 11      | 24,38 | 21,8  | T-       | 33  |        |       |          | 55  | -24,38 | -15,4 | DC-      |
| 12      |       |       |          | 34  |        |       |          | 56  | -24,38 | -12,2 | DC-      |
| 13      |       |       |          | 35  | 0,03   | 9     | U        | 57  | -24,38 | -9    | DC-      |
| 14      |       |       |          | 36  | 0,03   | 12,2  | U        | 58  | -24,38 | -5,8  | E4       |
| 15      |       |       |          | 37  | 0,03   | 15,4  | U        | 59  |        |       |          |
| 16      | 13,42 | -21,8 | g5       | 38  | 0,03   | 18,6  | U        | 60  | -24,38 | 0,7   | g4       |
| 17      |       |       |          | 39  | 0,03   | 21,8  | U        | 61  |        |       |          |
| 18      |       |       |          | 40  | -8,51  | -21,8 | W        | 62  | -24,38 | 7,1   | DC-      |
| 19      |       |       |          | 41  |        |       |          | 63  | -24,38 | 15,4  | DC-      |
| 20      |       |       |          | 42  |        |       |          | 64  | -24,38 | 18,6  | E2       |
| 21      |       |       |          | 43  |        |       |          | 65  | -24,38 | 21,8  | g2       |
| 22      | 8,38  | 2,6   | E3       | 44  | -12,23 | -9    | V        |     |        |       |          |

all values in mm



Pinout and Dimensions



Pinout

This is an electrostatic discharge sensitive device (ESDS) due to international standard IEC 61340.

## **\*IMPORTANT INFORMATION AND WARNINGS**

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